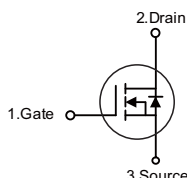


FEATURES

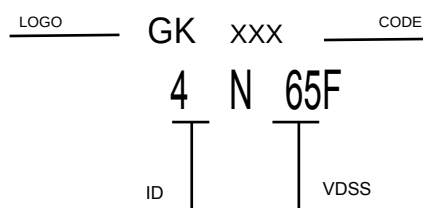
- 650V, 4 A
- $R_{DS(ON)} = 2.4 \Omega$ (Typ.) @ $V_{GS} = 10V$, $I_D = 2A$
- Fast Switching
- Improved dv/dt Capability
- 100% Avalanche Tested

APPLICATION

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS)
- Power Factor Correction (PFC)



V_{DSS} 650 V
 I_D 4 A
 $R_{DS(ON)}$ 2.4 Ω



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ C$ unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	4.0	A
Drain Current	Continuous	I_D	4.0	A
	Pulsed (Note 2)	I_{DM}	16	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	260	mJ
	Repetitive (Note 2)	E_{AR}	10.6	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation		P_D	36	W
Junction Temperature		T_J	+150	$^\circ C$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ C$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ C$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature

3. $L = 30mH$, $I_{AS} = 4A$, $V_{DD} = 50V$, $R_G = 25 \Omega$, Starting $T_J = 25^\circ C$

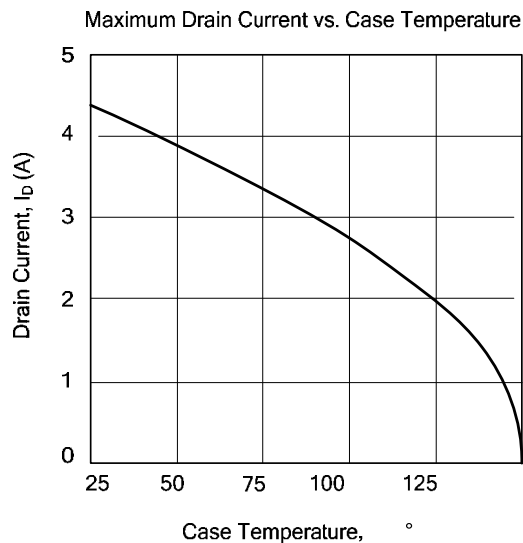
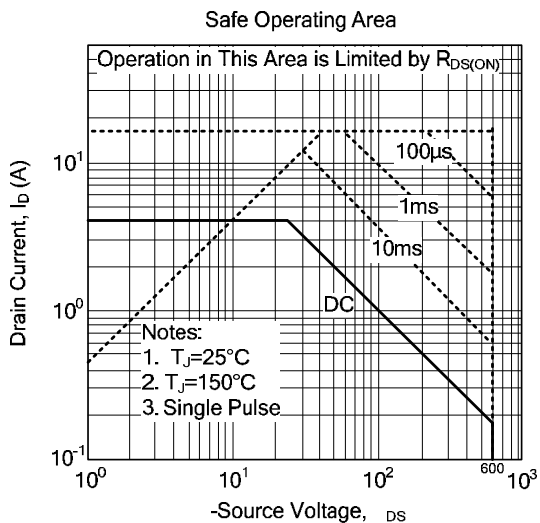
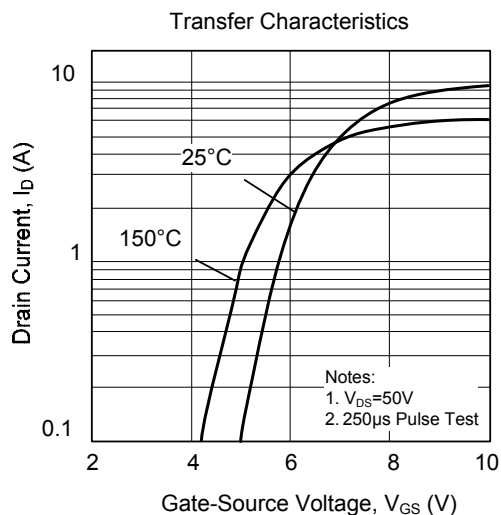
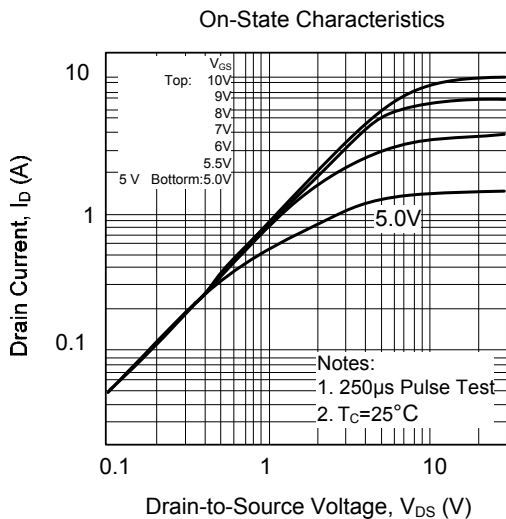
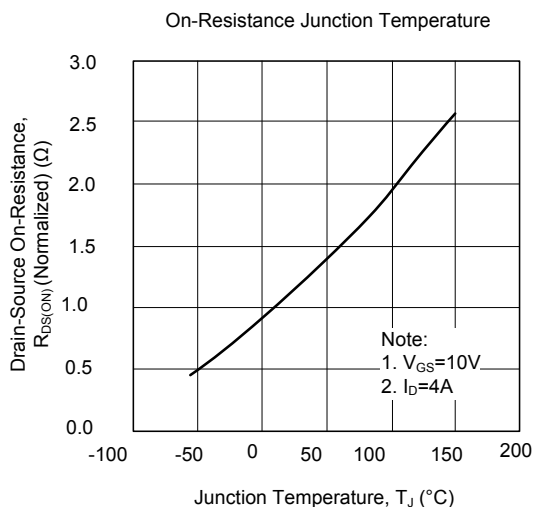
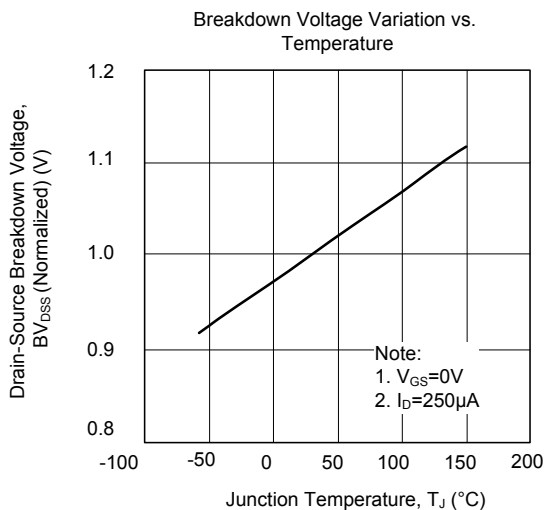
4. $I_{SD} \leq 4.4A$, $di/dt \leq 200A/\mu s$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ C$

Electrical Characteristics (T_c=25°C unless otherwise specified)

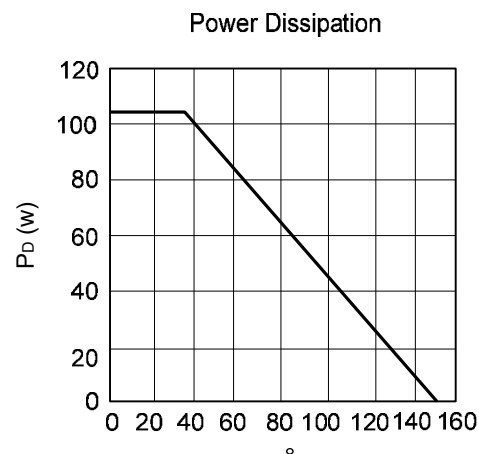
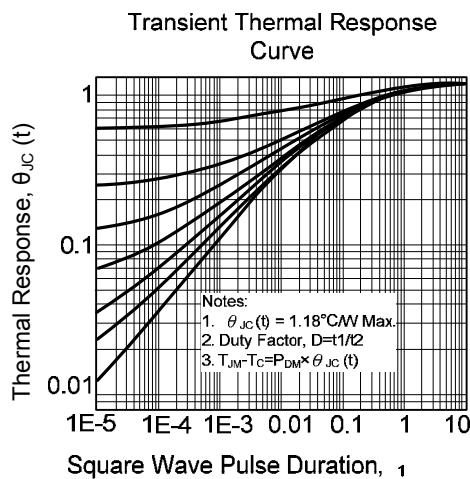
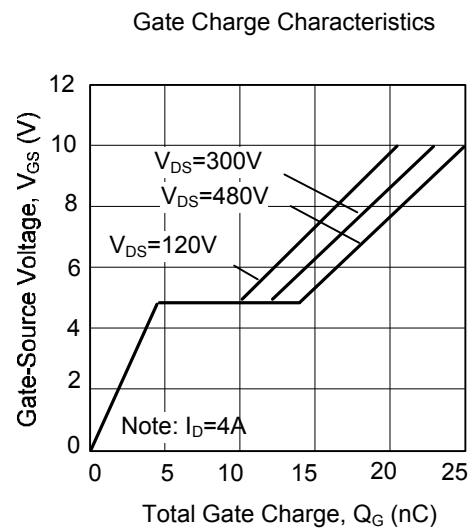
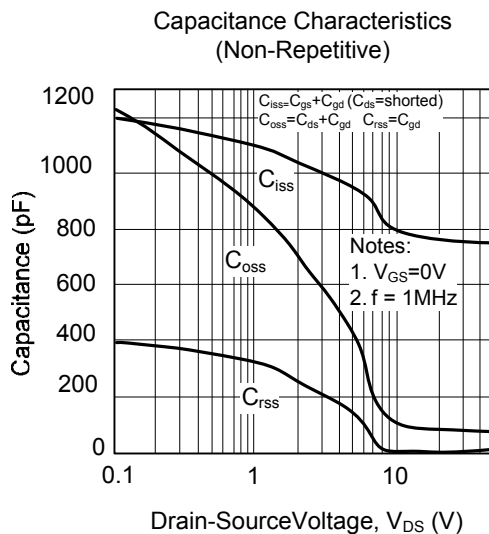
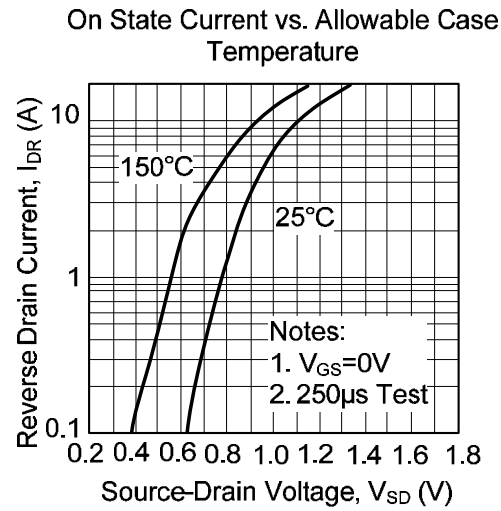
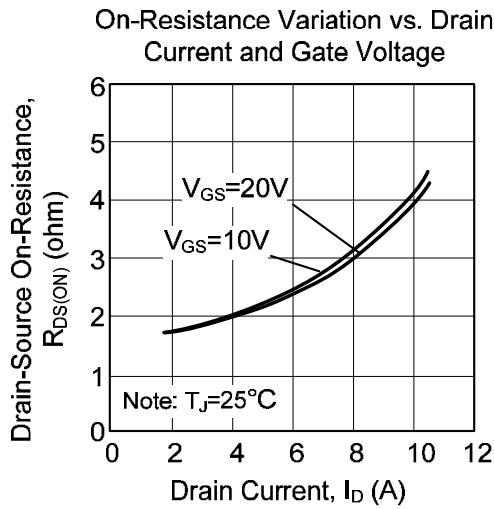
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0 V, I _D = 250μA	650			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
	Reverse		V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
Breakdown Voltage Temperature Coefficient		ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.6		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} = 10 V, I _D = 2A		2.4	2.8	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{DS} = 25 V, V _{GS} = 0V, f = 1MHz		520	670	pF
Output Capacitance		C _{OSS}			70	90	pF
Reverse Transfer Capacitance		C _{RSS}			8	11	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t _{D(ON)}	V _{DD} = 325V, I _D = 4.0A, R _G = 25Ω (Note 1, 2)		13	35	ns
Turn-On Rise Time		t _R			45	100	ns
Turn-Off Delay Time		t _{D(OFF)}			25	60	ns
Turn-Off Fall Time		t _F			35	80	ns
Total Gate Charge		Q _G	V _{DS} = 520V,I _D = 4A V _{GS} = 10V (Note 1, 2)		15	20	nC
Gate-Source Charge		Q _{GS}			3.4		nC
Gate-Drain Charge		Q _{GD}			7.1		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage		V _{SD}	V _{GS} = 0 V, I _S = 4.0A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I _S				4.4	A
Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}				17.6	A
Reverse Recovery Time		t _{rr}	V _{GS} = 0V, I _S = 4.0A,		250		ns
Reverse Recovery Charge		Q _{RR}	dI _F /dt = 100 A/μs (Note 1)		1.5		μC

Note: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

RATING AND CHARACTERISTIC CURVES

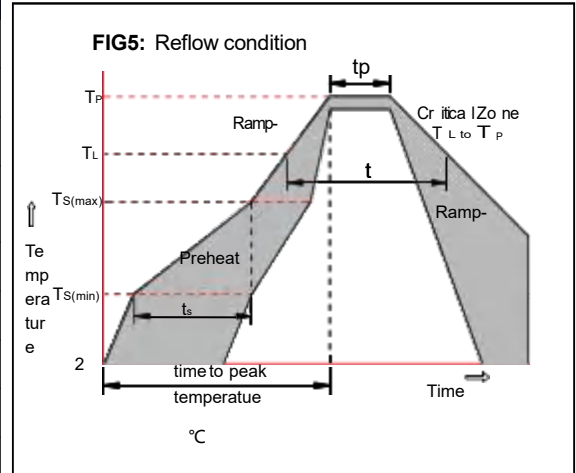


RATING AND CHARACTERISTIC CURVES



Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C



Package Dimensions & Suggested Pad Layout

